Central
Semiconductor Corp.
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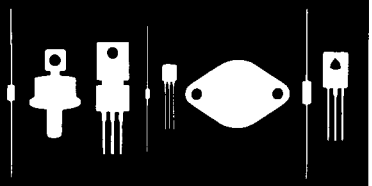
145 Adams Avenue
Hauppauge, New York 11788



2N3820
P-CHANNEL JUNCTION FET

JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3820 type is a Silicon P-Channel Junction Field Effect Transistor designed for low level amplifier applications.

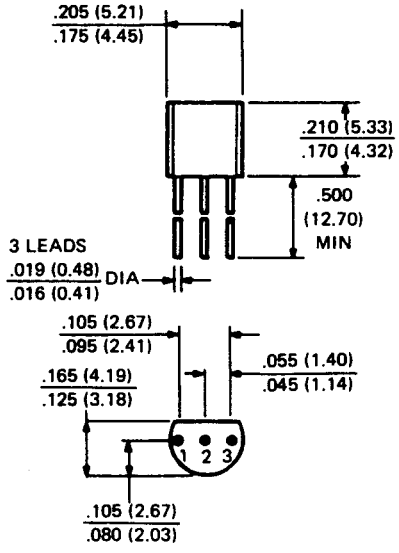
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNIT
Gate-Drain Voltage	V_{GD}	20	V
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage (Reverse)	V_{GS}	20	V
Gate Current	I_G	10	mA
Power Dissipation	P_D	360	mW
Operating and Storage Junction Temperature	T_J,T_{STG}	-65 TO +150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{GSS}	V_{GS}=10V		20	nA
I_{GSS}	V_{GS}=10V, T_A=100°C		2.0	µA
I_{DSS}	V_{DS}=10V	0.3	15	mA
BV_{GSS}	I_G=10µA	20		V
V_{GS}	V_{DS}=10V, I_D=30µA	0.3	7.9	V
$V_{GS(OFF)}$	V_{DS}=10V, I_D=10µA		8.0	V
C_{iss}	V_{DS}=10V, V_{GS}=0, f=1.0MHz		32	pF
C_{rss}	V_{DS}=10V, V_{GS}=0, f=1.0MHz		16	pF
|yfs|	V_{DS}=10V, V_{GS}=0, f=1.0kHz	800	5000	µmho
|yfs|	V_{DS}=10V, V_{GS}=0, f=10MHz	700		µmho
|yos|	V_{DS}=10V, V_{GS}=0, f=1.0kHz		200	µmho

OUTLINE DRAWING:



LEAD CODE:

1. DRAIN
2. GATE
3. SOURCE

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